

**UNITED STATES PATENT AND TRADEMARK OFFICE**

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**BEFORE THE PATENT TRIAL AND APPEAL BOARD**

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MICRON TECHNOLOGY, INC.,  
Petitioner

v.

YANGTZE MEMORY TECHNOLOGIES COMPANY, LTD.,  
Patent Owner

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Case No.: IPR2025-00245  
U.S. Patent No. 11,482,532  
Issue Date: October 25, 2022

Title: JOINT OPENING STRUCTURES OF THREE-DIMENSIONAL  
MEMORY DEVICES AND METHODS FOR FORMING THE SAME

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**PETITION FOR *INTER PARTES* REVIEW  
OF U.S. PATENT NO. 11,482,532  
PURSUANT TO 35 U.S.C. §§311-319 AND 37 C.F.R. §42**

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**II. MANDATORY NOTICES**

**A. Real Party-in-Interest**

Petitioner Micron Technology, Inc., and its subsidiaries, including Micron Consumer Products Group LLC, are the real parties-in-interest.

**B. Related Matters**

On July 12, 2024, YMTC asserted the '532 Patent and U.S. Patent Nos. 10,672,711, 10,879,164, 10,879,254, 10,886,291, 11,101,276, 11,145,666, 11,450,604, 11,568,941, 11,581,322, and 12,010,838 against Micron. On August 21, 2024, the litigation was consolidated with *Yangtze Memory Technologies Company, Ltd. v. Micron Technology, Inc. and Micron Consumer Products Group, LLC*, Case No. 3:23-cv-05792-RFL (N.D. Cal., filed November 9, 2023) (“Co-Pending Litigation”). U.S. Patent Nos. 10,658,378, 10,861,872, 10,868,031, 10,937,806, 10,950,623, 11,468,957, 11,501,822, and 11,600,342 were asserted by Patent Owner in the first filed case, leading to a total of 19 patents-at-issue in the now consolidated Co-Pending Litigation.

In addition to this Petition, Petitioner is filing (or has filed) petitions for *inter partes* review of each asserted patent in the Co-Pending Litigation:

Patent	PTAB Proceeding	Wave
10,658,378 (claims 15-17 and 19-20)	IPR2024-00788	Wave 1 Petitions
10,861,872 (claims 1-6 and 11-13)	IPR2024-00789	

## **XII. SECONDARY CONSIDERATIONS**

Petitioner is unaware of any applicable secondary considerations of nonobviousness. None were identified during prosecution. *See* generally Ex. 1002. Even if such considerations existed, none would overcome the strong *prima facie* showing of obviousness.

## **XIII. CONCLUSION**

Petitioner respectfully requests that the Board enter a final written decision finding the Challenged Claims unpatentable.

Respectfully submitted,

December 31, 2024

*/Jeremy Jason Lang/*

Jeremy Jason Lang

Reg. No. 73,064

1000 Marsh Road

Menlo Park, CA 94025-1015

T: (650) 614-7400

F: (650) 614-7401

Email: PTABDocketJLL2@orrick.com

*Attorney for Petitioner Micron Technology,  
Inc.*